

IN THE CLAIMS:

Please amend claim 1 as follows:

- Sub 01
1. (Amended) A method of forming wiring in a semiconductor device, comprising the steps of:
- forming a polysilicon layer on an insulating film formed on a semiconductor substrate;
- forming a metal layer on said polysilicon layer;
- depositing a nitride film on said metal layer by a low-pressure chemical vapor deposition method to form a hard mask layer ;
- AS
- patterning said hard mask layer to form a patterned hard mask;
- patterning said metal layer and said polysilicon layer using the patterned hard mask to form a patterned metal layer and said polysilicon layer; and
- depositing a nitride film by a low-pressure chemical vapor deposition method and then etching to form a spacer at a sidewall of the patterned metal layer, the patterned polysilicon layer and the patterned hard mask.